● General Description

The AGM315MBP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

● Features

- ■ Advance high cell density Trench technology
- ■Low $R_{DS(ON)}$ to minimize conductive loss
- ■Low Gate Charge for fast switching
- ■Low Thermal resistance

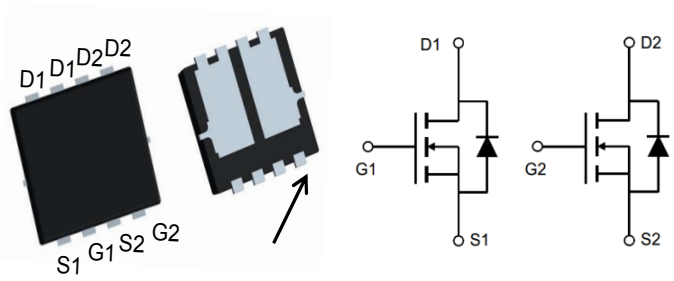
●Application

- ■MB/VGA Vcore
- ■SMPS 2nd Synchronous Rectifier
- ■POL application
- ■BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
30V	12mΩ	15A

PDFN3.3X3.3 Pin Configuration



Package Mark ing and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM315MBP	AGM315MBP	DFN3.3*3.3	325mm	16mm	5000

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	T_C = 25°C	I_D	15	A
	T_C = 100°C		11	
Pulsed Drain Current (Note 2)		I_{DM}	80	A
Total Power Dissipation @ T_C = 25°C		P_{DTOT}	20	W
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	14	mJ
Single Pulsed Avalanche Current (Note 3)		I_{AS}	17	A
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\Theta JC}$	6.4	°C/W
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)						
PARAMETER	**CONDITIONS**	**SYMBOL**	**MIN**	**TYP**	**MAX**	**UNIT**
Static (Note 4)						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	BV_{DSS}	30	--	--	V
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	$V_{GS(TH)}$	1.2	1.5	2.5	V
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V_{DS} = 30V, V_{GS} = 0V	I_{DSS}	--	--	1	μA
	V_{DS} = 24V, Tc = 125ºC		--	--	10	
Drain-Source On-State Resistance	V_{GS} = 10V, I_D = 10A	$R_{DS(on)}$	--	12	16	mΩ
	V_{GS} = 4.5V, I_D = 6A		--	19	25	
Forward Transconductance	V_{DS} = 5V, I_D = 6A	g_{fs}	--	13	--	S
Dynamic (Note 5)						
Total Gate Charge	V_{DS} = 15V, I_D = 8A, V_{GS} = 4.5V	Q_g	--	4.1	--	nC
Gate-Source Charge		Q_{gs}	--	1	--	
Gate-Drain Charge		Q_{gd}	--	2.1	--	
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	345	--	pF
Output Capacitance		C_{oss}	--	55	--	
Reverse Transfer Capacitance		C_{rss}	--	32	--	
Switching (Note 6)						
Turn-On Delay Time	V_{DD} = 15V, I_D = 1A, R_{GEN} =6Ω	$t_{d(on)}$	--	2.8	--	ns
Turn-On Rise Time		t_r	--	7.2	--	
Turn-Off Delay Time		$t_{d(off)}$	--	15.8	--	
Turn-Off Fall Time		t_f	--	4.6	--	

Notes:

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. L = 0.1mH, I_{AS} = 17A, V_{DD} = 25V, R_G = 25Ω, Starting T_J = 25°C
4. Pulse test: PW ≤ 300μs, duty cycle ≤ 2%
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

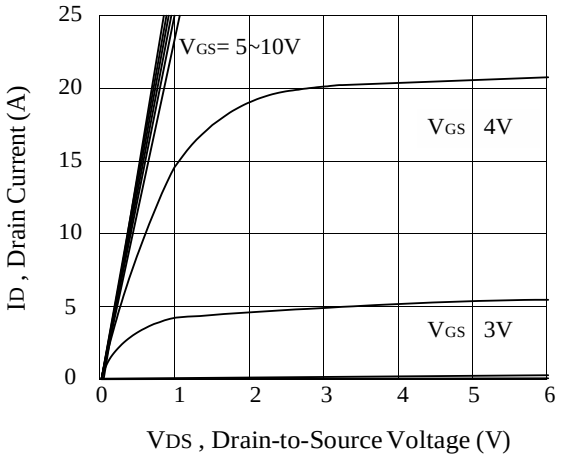


Figure 1. Output Characteristics

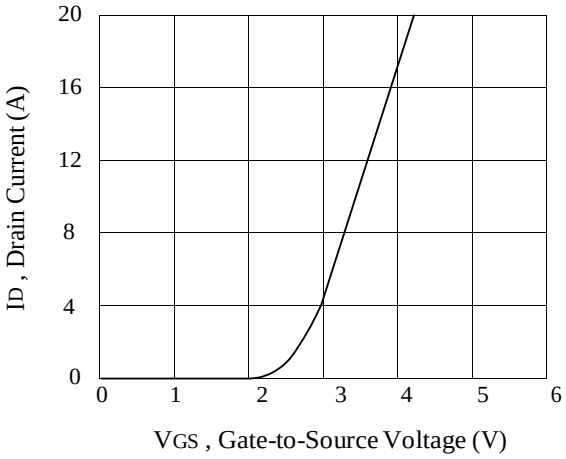


Figure 2. Transfer Characteristics

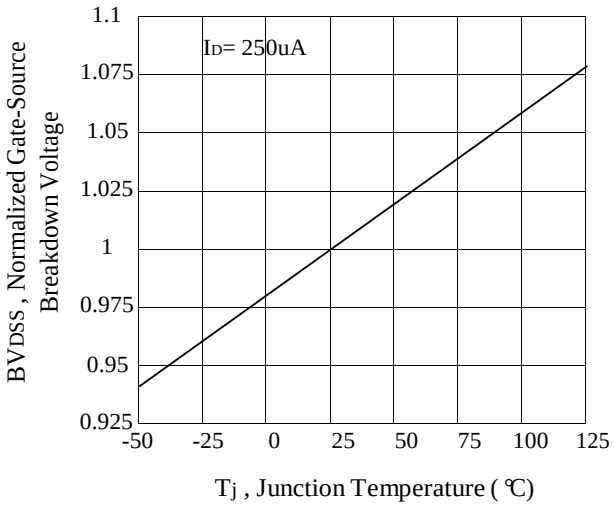


Figure 3. Breakdown Voltage Variation with Temperature

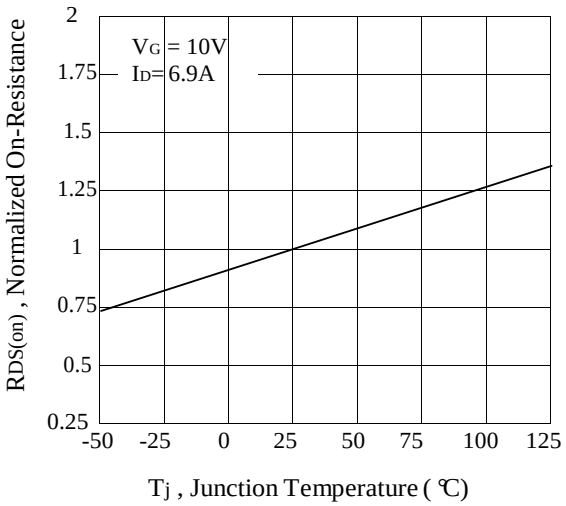


Figure 4. On-Resistance Variation with Temperature

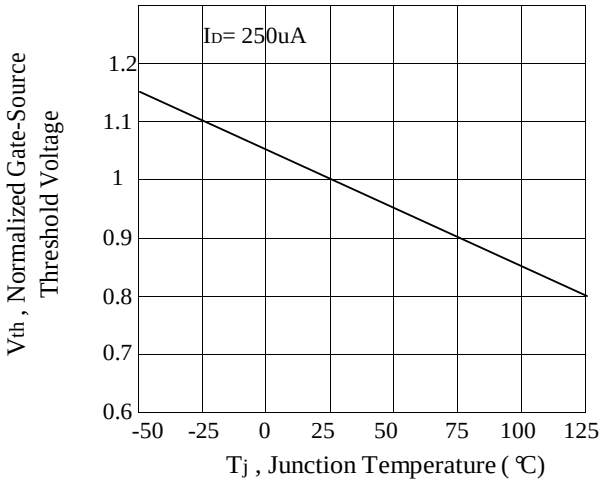


Figure 5. Gate Threshold Variation with Temperature

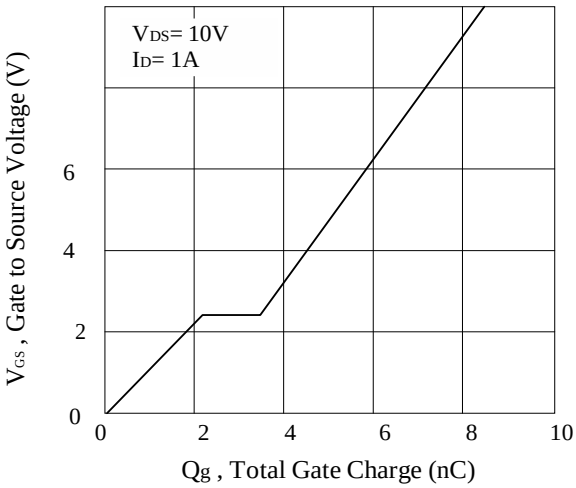
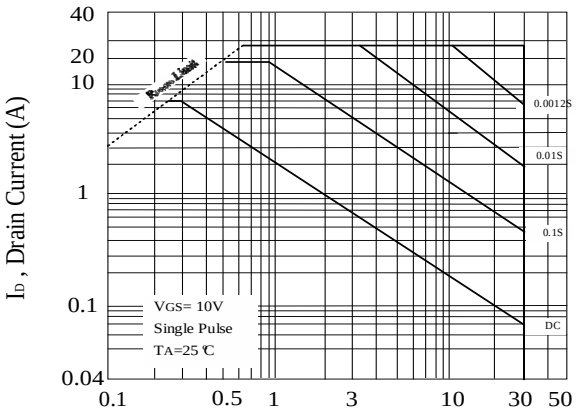
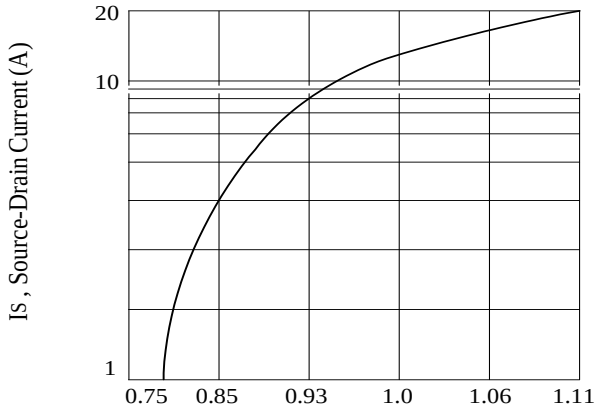


Figure 6. Gate Charge



VDS , Drain-Source Voltage (V)

Figure 7. Maximum Safe Operating Area



VSD , Body Diode Forward Voltage (V)

Figure 8. Body Diode Forward Voltage Variation with Source Current

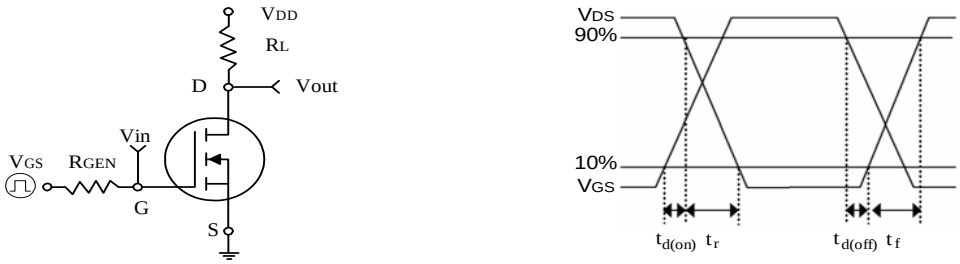
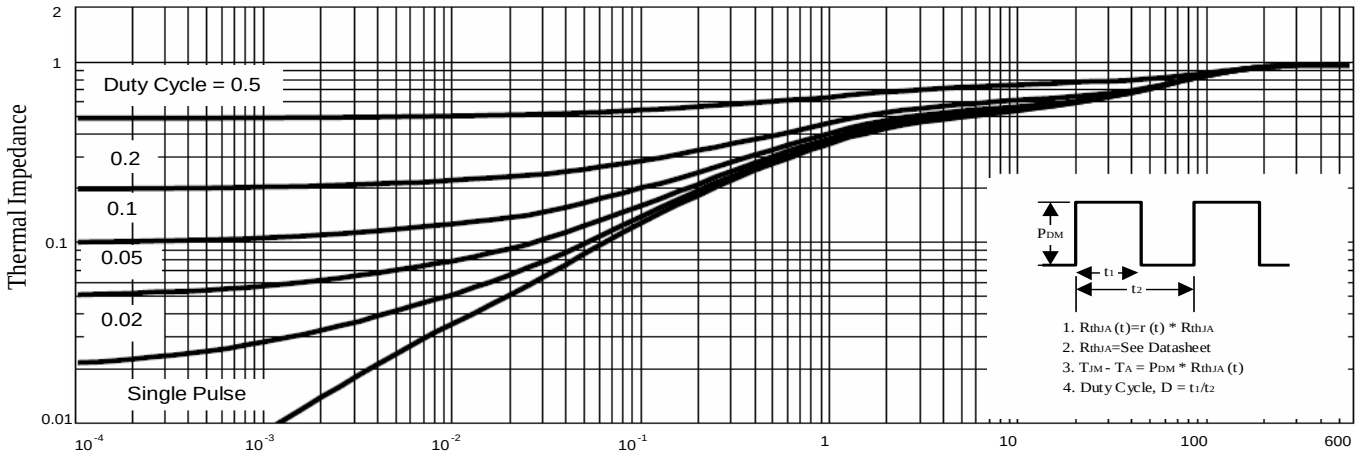


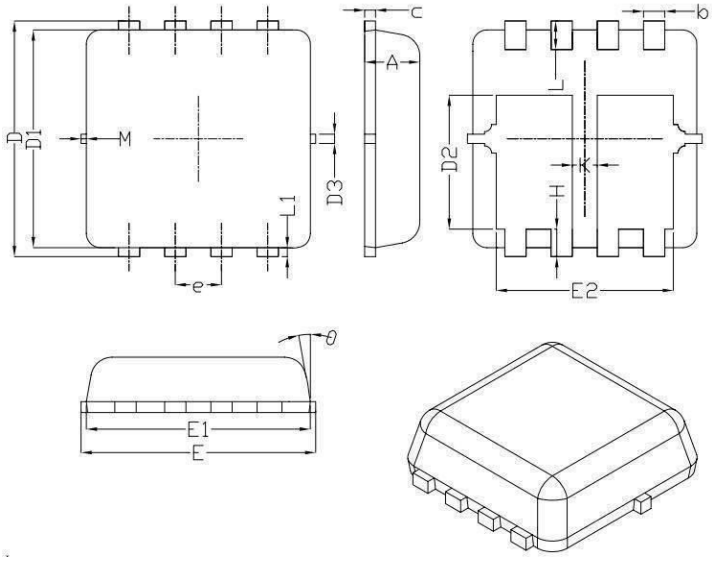
Figure 9. Switching Test Circuit and Switching Waveforms



Square Wave Pulse Duration (sec)

Figure 10. Normalized Thermal Transient Impedance Curve

●Dimensions（DFN3.3×3.3）



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	--	0.13	--
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e		0.65 BSC	
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	--	0.13	--
K	0.30	--	--
θ	--	10°	12°
M	*	*	0.15

* Not Specified

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This document is the second version issued on October 10, 2019. This document replaces andReplace all previously provided information.